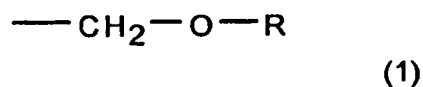


## CLAIMS

1. A polymer compound comprising:

an alkali soluble group (i), wherein

5 at least one hydrogen atom of a hydroxyl group in the alkali soluble group (i) is protected by an acid dissociable, dissolution inhibiting group (ii) represented by a general formula (1):



(wherein R represents an organic group containing no more than 20 carbon

10 atoms and at least one hydrophilic group), and

the polymer compound exhibits changed alkali solubility under the action of acid.

2. A polymer compound according to claim 1, wherein the alkali soluble group (i)

15 is at least one selected from an alcoholic hydroxyl group, a phenolic hydroxyl group, or a carboxyl group.

3. A polymer compound according to claim 2, wherein a carbon atom adjacent to the carbon atom connected to the alcoholic hydroxyl group is bonded to at least one

20 fluorine atom.

4. A polymer compound according to claim 1, wherein the hydrophilic group is at least one selected from a carbonyl group, an ester group, an alcoholic hydroxyl group, ether, an imino group, or an amino group.

5. A photoresist composition comprising:

a base material resin component (A) which exhibits changed alkali solubility under the action of acid; and

5 an acid generator component (B) which generates the acid on exposure to radiation, wherein

the base material resin component (A) is the polymer compound according to any one of claims 1 to 4.

10 6. A resist pattern formation method comprising:

forming a photoresist film on a substrate using the photoresist composition according to claim 5;

exposing the photoresist film; and

developing the exposed photoresist film to form a resist pattern.

15